

■ PRODUCT CHARACTERISTICS

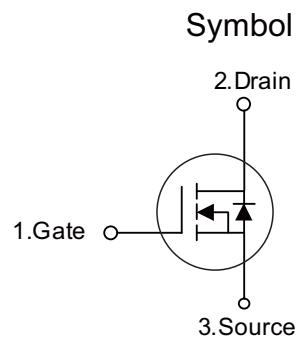
VDSS	700V
R _{DS(on)Typ(@V_{GS} =10 V)}	1Ω
Qg@type	44nC
ID	10A

■ APPLICATIONS

- High frequency switching mode power supply
- Electronic ballast
- UPS

■ FEATURES

- * Ultra low gate charge
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness



■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT10N70F	TO-220F	50 pieces/Tube
N/A	MOT10N70A	TO-220	50 pieces/Tube

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	700	V
Gate-Source Voltage		V _{GSS}	±30	V
Drain Current	Continuous	I _D	10	A
	Pulsed (Note 2)	I _{DM}	40	A
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	120	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.6	V/ns
Power Dissipation	TO-220	P _D	150	W
	TO-220F		35	W
Junction Temperature		T _J	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. L = 10mH, I_{AS} = 5.0A, V_{DD} = 50V, R_G = 25 Ω Starting T_J = 25°C

4. I_{SD} ≤ 10A, di/dt ≤200A/μs, V_{DD} ≤BV_{DSS}, Starting T_J = 25°C

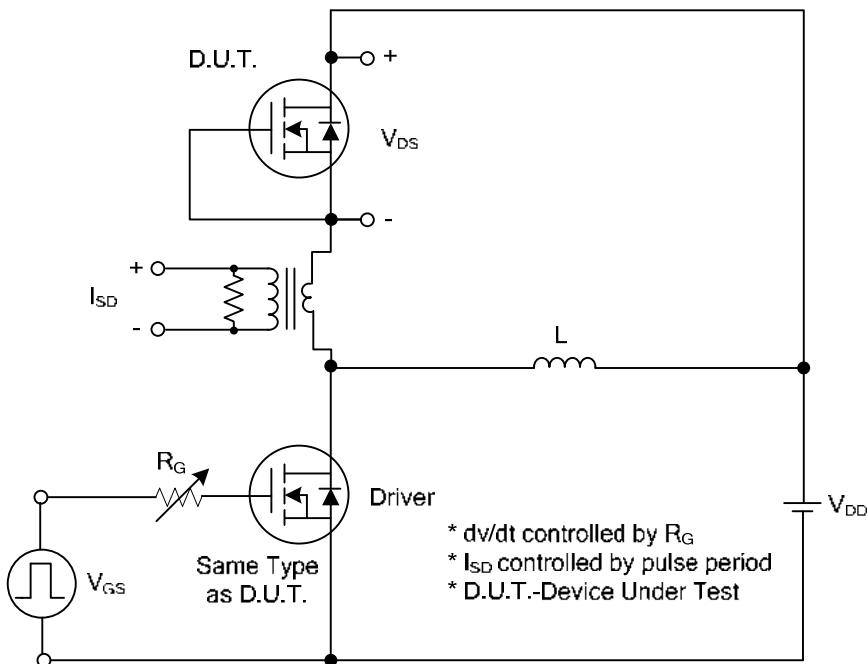
■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Off characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=250\mu\text{A}$	700	-	-	V
Drain-Source Leakage Current	I_{DSS}	$\text{V}_{\text{DS}}=700\text{V}, \text{V}_{\text{GS}}=0\text{V}$	-	-	10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	$\text{V}_{\text{GS}}=30\text{V}, \text{V}_{\text{DS}}=0\text{V}$	-	100	nA
	Reverse		$\text{V}_{\text{GS}}=-30\text{V}, \text{V}_{\text{DS}}=0\text{V}$	-	-100	nA
On characteristics						
Gate Threshold Voltage	$\text{V}_{\text{GS(TH)}}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_D=250\mu\text{A}$	2.0	-	4.0	V
Static Drain-Source On-State Resistance	$\text{R}_{\text{DS(ON)}}$	$\text{V}_{\text{GS}}=10\text{V}, \text{I}_D=5.0\text{A}$	-	1	1.1	Ω
Dynamic characteristics						
Input Capacitance	C_{ISS}	$\text{V}_{\text{GS}}=0\text{V}, \text{V}_{\text{DS}}=25\text{V}, f=1.0 \text{ MHz}$	-	1400	-	pF
Output Capacitance	C_{OSS}		-	142	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	10.4	-	pF
Switching characteristics						
Total Gate Charge (Note 1)	Q_G	$\text{V}_{\text{DS}}=100\text{V}, \text{V}_{\text{GS}}=10\text{V}, \text{I}_D=10\text{A}$	-	42	-	nC
Gatesource Charge	Q_{GS}		-	7.8	-	nC
Gate-Drain Charge	Q_{GD}		-	6.6	-	nC
Source-drain diode ratings and characteristics						
Maximum Continuous Drain-Source Diode Forward Current	I_S	$\text{V}_{\text{DS}}=100\text{V}, \text{V}_{\text{GS}}=10\text{V}, \text{I}_D=10\text{A}, \text{R}_G=25\Omega$ (Note 1, 2)	-	12	-	ns
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}		-	19	-	ns
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}		-	92	-	ns
Reverse Recovery Time (Note 1)	t_{rr}		-	41	-	ns
Reverse Recovery Charge	Q_{rr}	$\text{dI}_F/\text{dt}=100\text{A}/\mu\text{s}$ (Note1)	-	368	-	ns
			-	4.6	-	μC

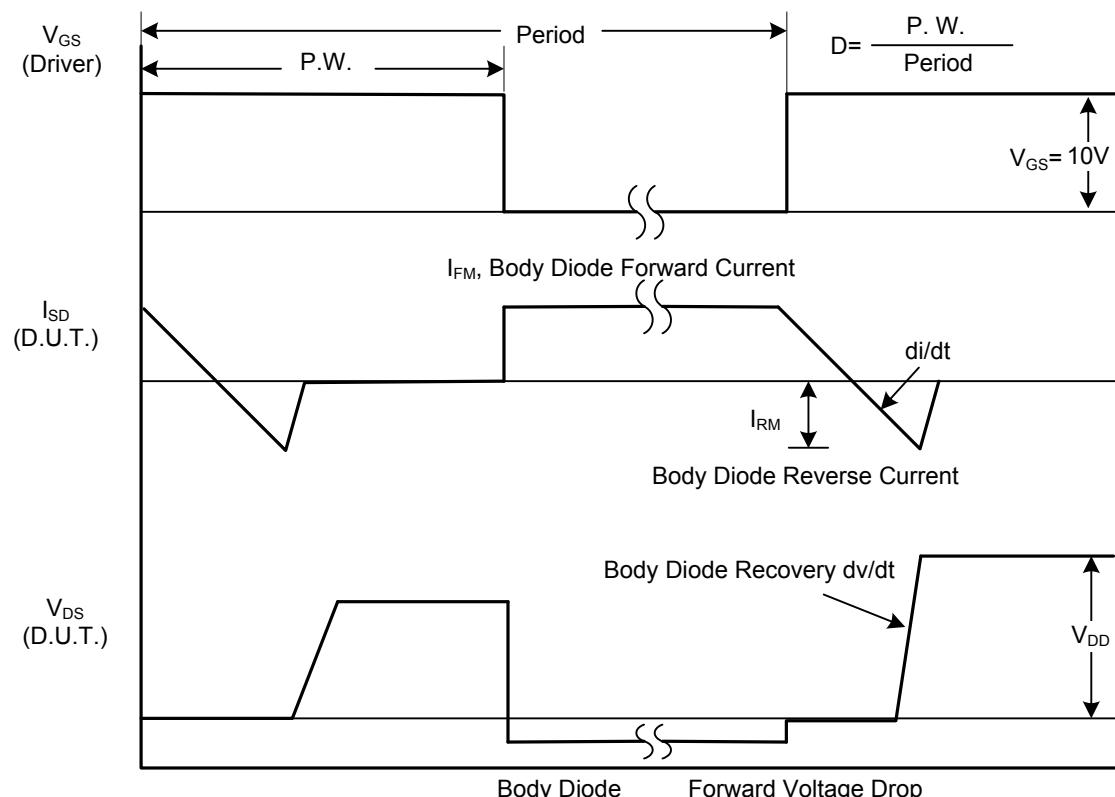
Notes: 1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

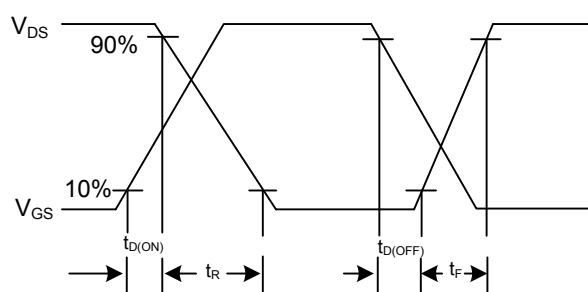
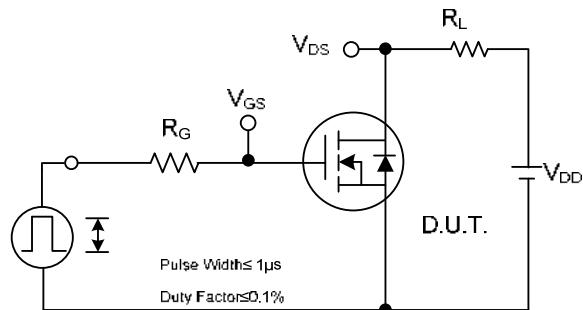


Peak Diode Recovery dv/dt Test Circuit



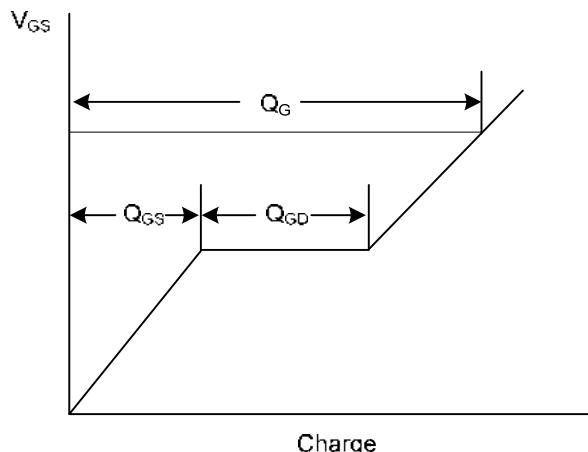
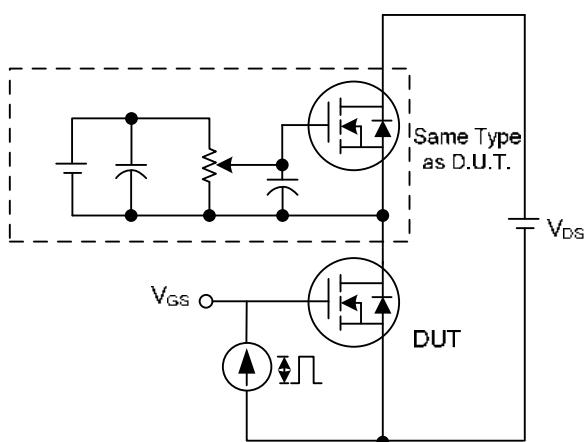
Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS(Cont.)



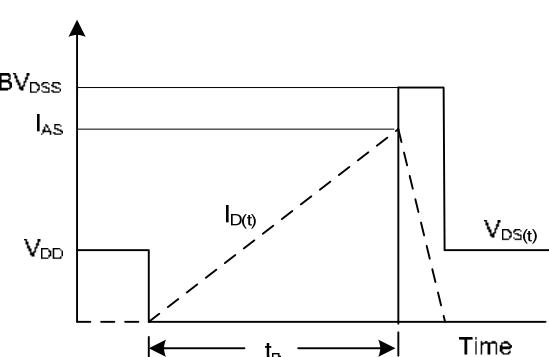
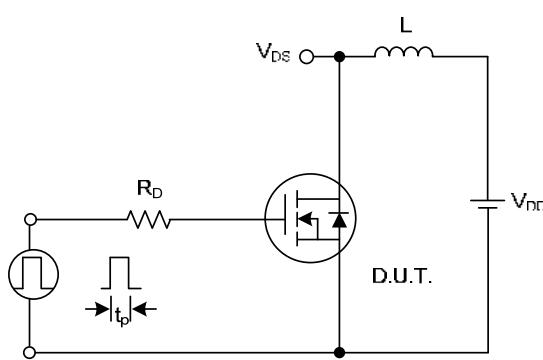
Switching Test Circuit

Switching Waveforms



Gate Charge Test Circuit

Gate Charge Waveform

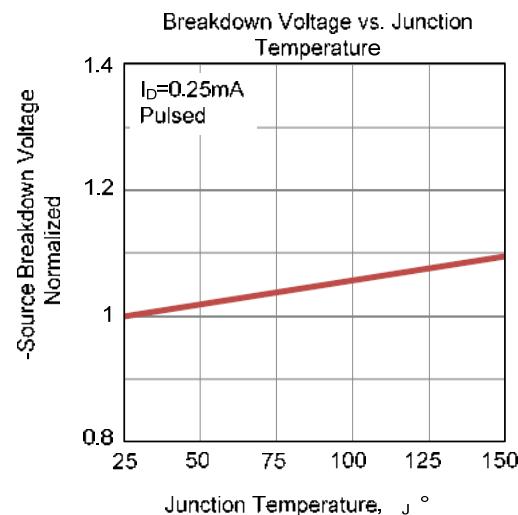
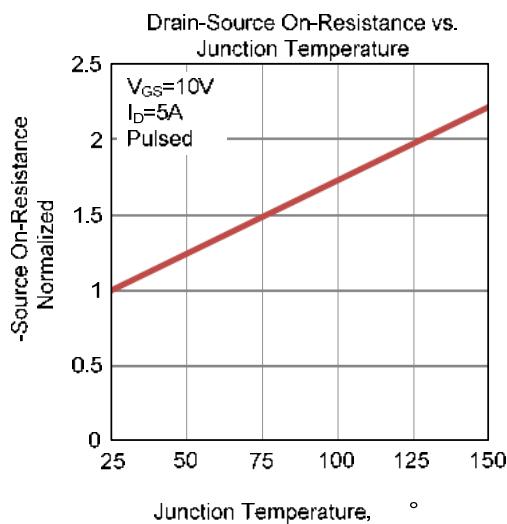
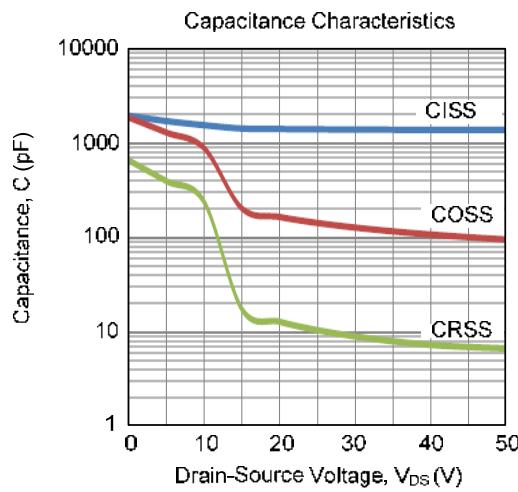
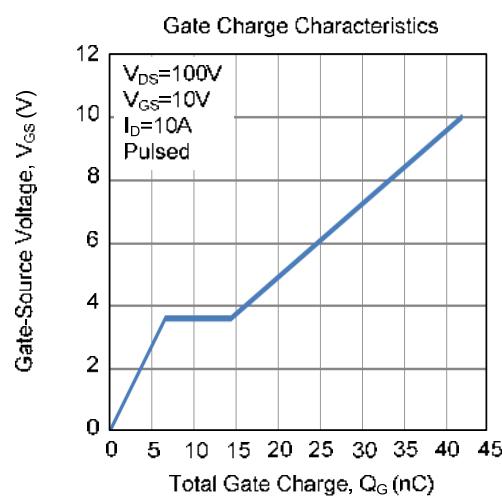
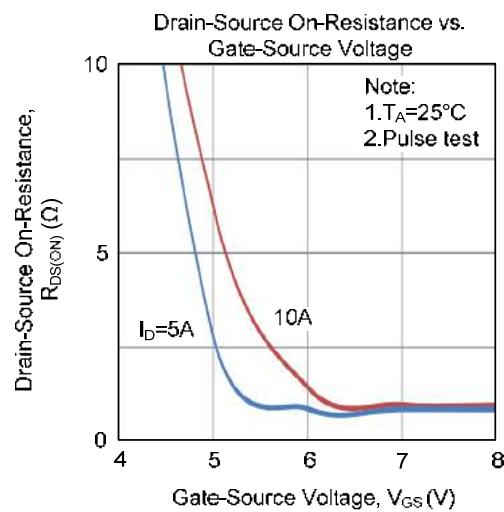
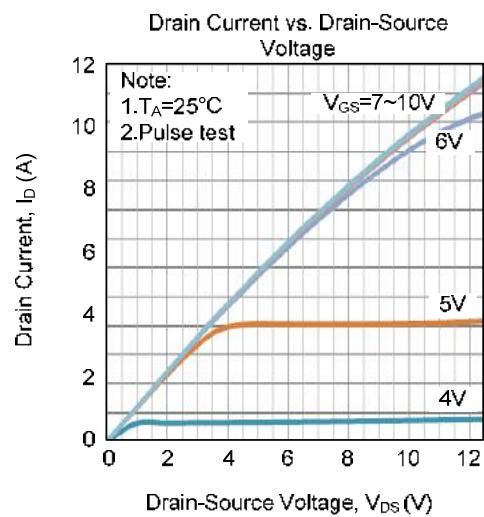


Unclamped Inductive Switching Test Circuit

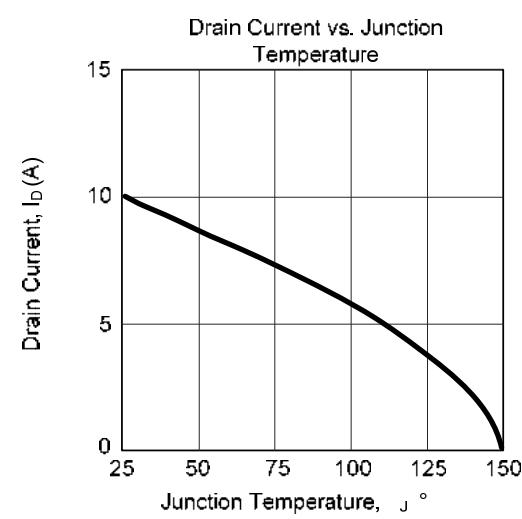
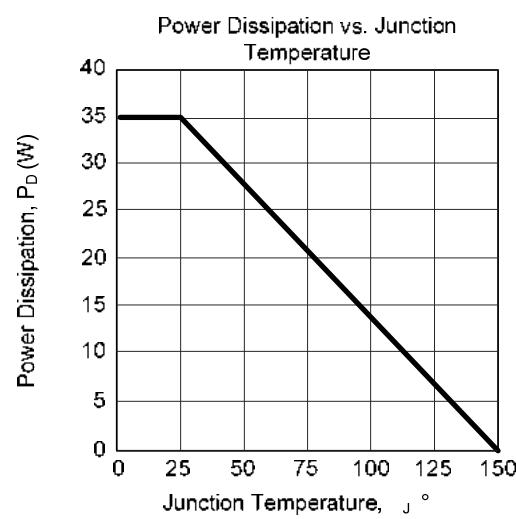
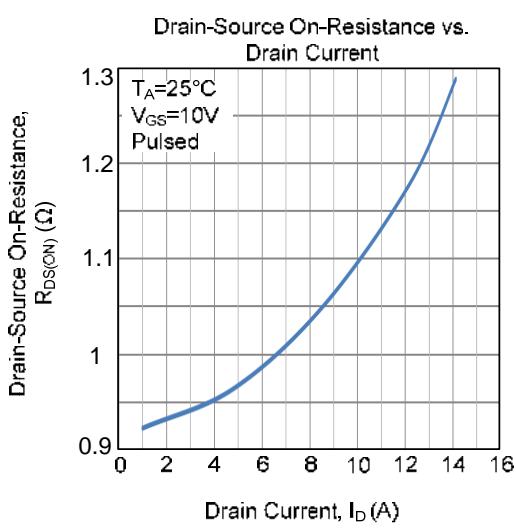
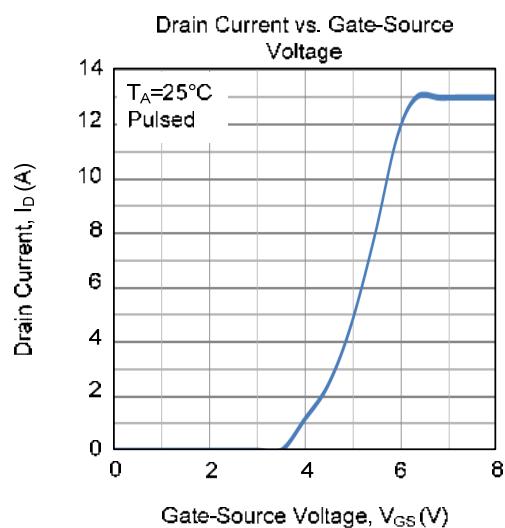
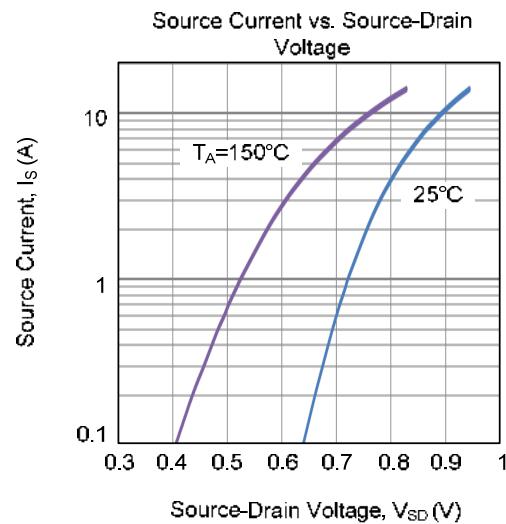
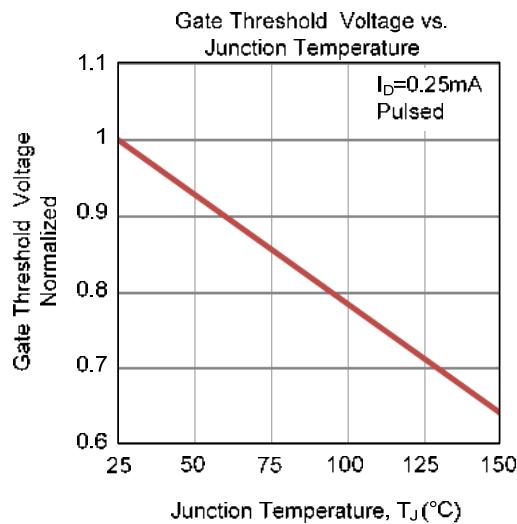
Unclamped Inductive Switching Waveforms



■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)

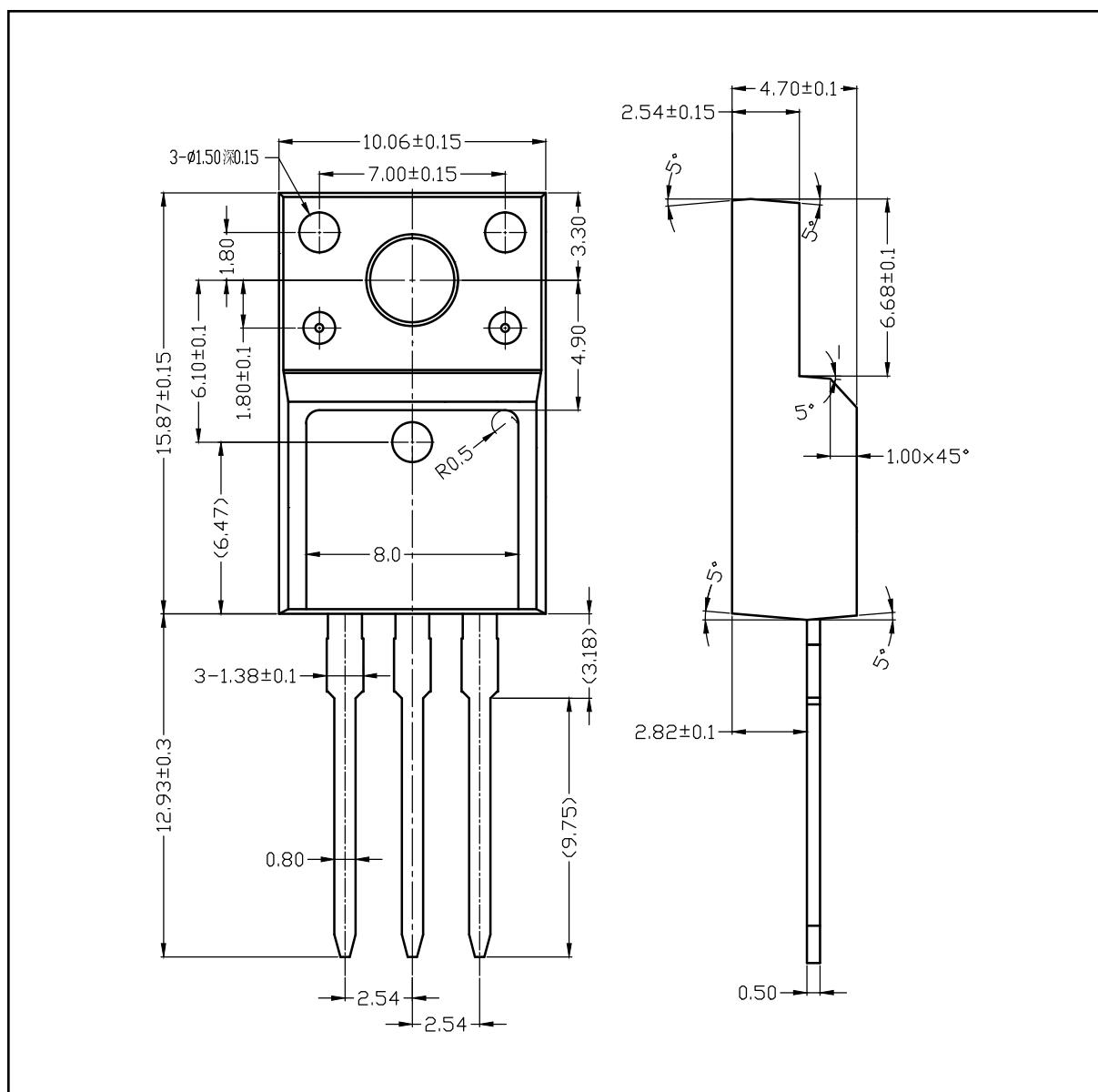




仁懋电子

MOT10N70A
MOT10N70F
N-CHANNEL MOSFET

■ TO-220F-3L PACKAGE OUTLINE DIMENSIONS



■ TO-220-3L PACKAGE OUTLINE DIMENSIONS

